# PUB4219 (PU4219), PUB4519 (PU4519)

## Silicon PNP epitaxial planar type darlington

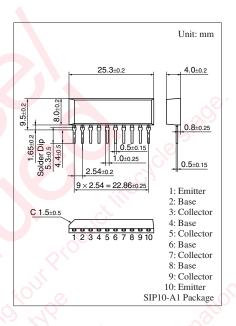
For power amplification Complementary to PUB4119 (PU4119), PUB4419 (PU4419)

#### ■ Features

- High forward current transfer ratio h<sub>FE</sub>
- High-speed switching
- PUB4219 (PU4219): PNP 4 elements PUB4519 (PU4519): PNP 2 elements × 2

### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-60	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-60	V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-5	V
Collector current	$I_C$	-2	A
Peak collector current	I <sub>CP</sub>	-4	A
Collector power dissipation	$P_{C}$	15	W
$T_a = 25^{\circ}C$		3.5	
Junction temperature	$T_j$	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C



## ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

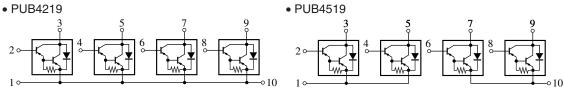
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = -30 \text{ mA}, I_B = 0$	-60	×0		V
Base-emitter voltage	V <sub>BE</sub>	$V_{CE} = -4 \text{ V}, I_{C} = -2 \text{ A}$	AY.	10	-2.8	V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -60 \text{ V}, I_E = 0$		·	J)−1	mA
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -30 \text{ V}, I_{B} = 0$	10°	N)	-2	mA
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_C = 0$		<b>8</b>	-2	mA
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = -4 \text{ V}, I_{C} = -1 \text{ A}$	1 000			_
	h <sub>FE2</sub> *	$V_{CE} = -4 \text{ V}, I_{C} = -2 \text{ A}$	1 000		10 000	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -2 \text{ A}, I_B = -8 \text{ mA}$			-2.5	V
Transition frequency f <sub>T</sub> V <sub>Cl</sub>		$V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time	t <sub>on</sub>	$I_C = -2 A$		0.4		μs
Storage time	t <sub>stg</sub>	$I_{B1} = -8 \text{ mA}, I_{B2} = 8 \text{ mA}$		1.5		μs
Fall time	t <sub>f</sub>	$V_{CC} = -50 \text{ V}$		0.5		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

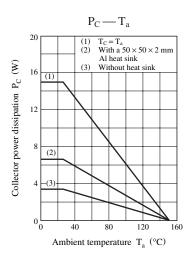
#### 2. \*: Rank classification

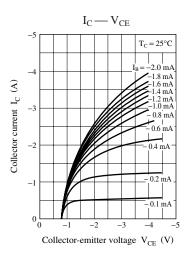
Rank	Free	P.S	Q	
$h_{FE}$	1000 to 10000	2 000 to 10 000	1000 to 5000	

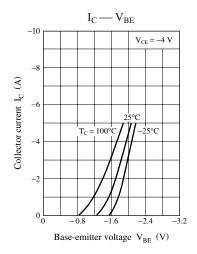
### ■ Internal Connection

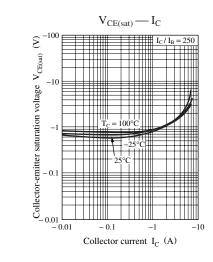


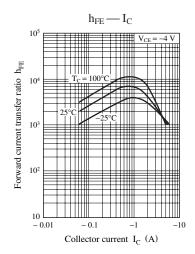
Note) The part numbers in the parenthesis show conventional part number.

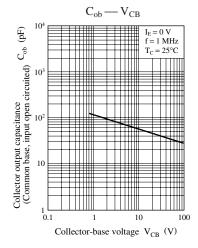


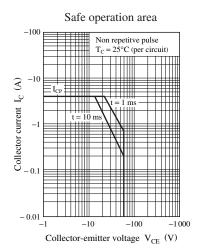












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